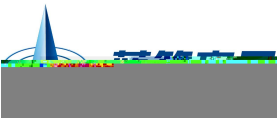


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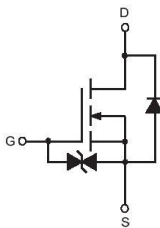


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SOT-23 F G G H N I J MOS K L M N ON-CHANNEL MOSFET in a SOT-23 Plastic Package.

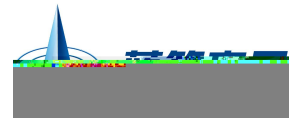
P Q % R - S T U V W X Y Z % [\ V W O] V ^ _ ` 2KVO < = B C O
Sensitive gate trigger current and Low Holding current.ESD protected up to 2KV. HF product.

a b c d % e f X g h R - O
Intenl q for use in general purpose switching and phase control applications



PIN1 i G PIN 2 i S PIN 3 i D

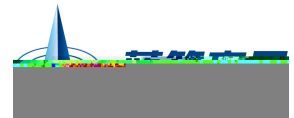
Marking	H702K
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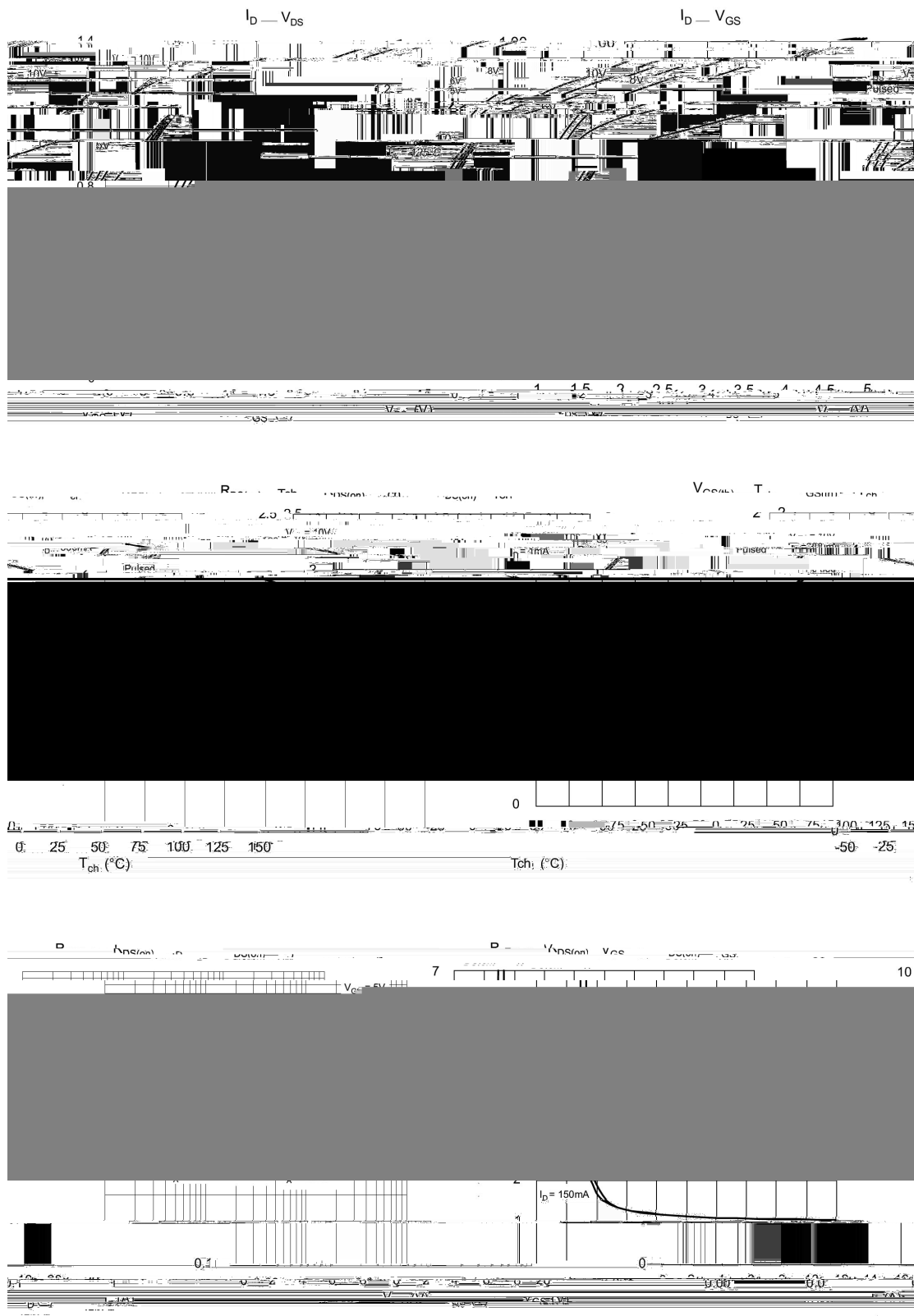
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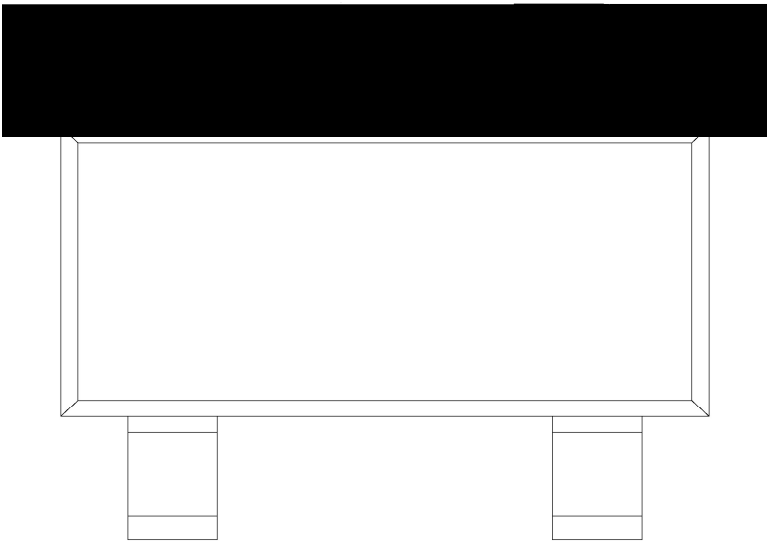
j k Parameter	l m Symbol	k n Rating	o h Unit
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage	V_{DGR}	60	V
Drain Current - Continuous	I_D	300	mA
Drain Current - Pulsed	I_{DM}	800	mA
Gate-Source Voltage - Continuous	V_{GSS}	± 20	V
Power Dissipation	P_D	350	mW
Storage Temperature Range	T_{stg}	-55~150	$^{\circ}\text{C}$

j k Parameter	l m Symbol	p q r s Test Conditions		t u n Min	v w n Typ	t x n Max	o h Unit
Drain-Source Breakdown Voltage	V_{DSS}	$V_{GS}=0$	$I_D=10\mu\text{A}$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0$	$V_{DS}=60\text{V}$			1.0	μA
Gate-Source Leakage current	I_{GSS}	$V_{DS}=0\text{V}$	$V_{GS}=\pm 20\text{V}$			± 10	μA
Static Drain-Source On-Resistance	$R_{DS(on)(1)}$	$V_{GS}=10\text{V}$	$I_D=0.5\text{A}$			5	Ω
	$R_{DS(on)(2)}$	$V_{GS}=5\text{V}$	$I_D=0.05\text{A}$			5.5	Ω
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}$	$I_S=250\text{mA}$			1.5	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$	$I_D=250\mu\text{A}$	1.0	1.6	2.5	V
Forward Transconductance	Y_{fs}	$V_{DS}=10\text{V}$	$I_D=0.2\text{A}$	80			ms
Drain-Source On-Voltage	$V_{DS(on)(1)}$	$V_{GS}=10\text{V}$	$I_D=500\text{mA}$			2.5	V
	$V_{DS(on)(2)}$	$V_{GS}=5.0\text{V}$	$I_D=50\text{mA}$			0.275	V
Turn-On Time	$t_{d(on)}$	$V_{DD}=25\text{V}$ $R_G=25\Omega$ $V_{gen}=10\text{V}$	$I_D=500\text{mA}$ $R_L=25\Omega$			20	ns
Turn-Off Time	$t_{d(off)}$					40	ns
Input Capacitance	C_{iss}					50	pF
Output Capacitance	C_{oss}	$V_{ds}=25\text{V}$ $f=1\text{MHz}$	$V_{GS}=0\text{V}$			25	pF
Reverse Transfer Capacitance	C_{rss}					5	pF

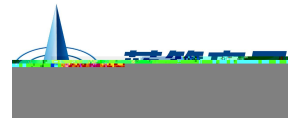


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y z i
H i { | } ~ '
702K i { w m ~ '
Note:
H:



Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

- 1 150 180 60 90sec;
- 2 245±5 5±0.5sec;
- 3 2 10°C/sec.

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

260±5°C

10±1 sec.

Temp.:260±5°C

Time:10±1 sec